

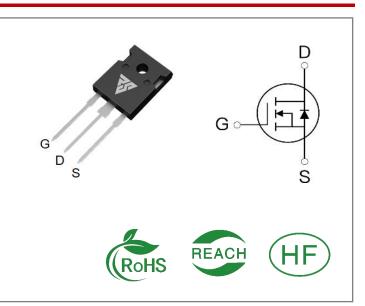
ID	R _{Ds} (ON)(Typ)	VDSS
25A	0.18Ω	500V

Applications:

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Features:

- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability



Ordering Information

Part Number	Package	Marking	Packing	Qty.
RS25N50W	T0-247-3	RS25N50W	Tube	30 PCS

Absolute Maximun Ratings Tc= 25° C unless otherwise specified

Symbol	Parameter	RS25N50W	Units
VDSS	Drain-to-Source Voltage	500	V
ID	Continuous Drain Current TC=25 $^\circ\!\!\mathbb{C}$	25	٨
IDM	Pulsed Drain Current (Note*1)	100	A
PD	Power Dissipation	190	W
VGS	Gate- to- Source Voltage	±30	V
EAS	Single Pulse Avalanche Engergy L = 10mH,,VDD = 50V, RG = 25Ω	671	mJ
	Maximum Temperature for Soldering		
TL TPKG	Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds	300 260	Ĉ
TJ and TSTG	Operating Junction and Storage Temperature Range	-55 to 150	

* Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the" Absolute Maximum Ratings" Table may cause permanent damage to the device.



Thermal Resistance

Symbol	Parameter	RS25N50W	Units	Test Conditions
RθJC	Junction-to-Case	0.65	°C/W	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 1 5 0 $^\circ\!\!C$
RθJA	Junction-to- Ambient	62.5		1 cubic foot chamber,free air.

OFF Characteristics TJ= 25° C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	500			V	VGS=0V,ID=250μ Α
IDSS	Drain- to- Source Leakage Current			1	μA	VDS=500V,VGS= 0V
	Gate- to- Source Forward Leakage			100	~ ^	VGS=30V ,VDS=0 V
IGSS	Gate- to- Source Reverse Leakage			-100	nA	VGS=-30V ,VDS= 0V

ON Characteristics TJ=25°C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On- Resistance(Note*2)		0.18	0.24	Ω	VGS=10V,ID=12. 5A
VGS(TH)	Gate Threshold Voltage	3		4	V	VGS=VDS,ID=25 0μA

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time		53			
trise	Rise Time		37			VDS=250V
td(OFF)	Turn- OFF Delay Time		221		nS	ID=25A RG=25Ω
tfall	Fall Time		70			



Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
Ciss	Input Capacitance		3134			VGS=0V
Coss	Output Capacitance		340		pF	VDS=25V
Crss	Reverse Transfer Capacitance		13			f=1.0MHz
Qg	Total Gate Charge		60.5			VDS=400V
Qgs	Gate- to- Source Charge		15.5		nC	ID=25A
Qgd	Gate-to-Drain(" Miller") Charge		22			VGS=10V

Dynamic Characteristics Essentially independent of operating temperature

Source- Drain Diode Characteristics

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
IS	Continuous Source Current			25	А	Integral pn- diode
ISM	Maximum Pulsed Current			100	А	in MOSFET
VSD	Diode Forward Voltage			1.4	V	IS=12.5A,VGS=0V
trr	Reverse Recovery Time		375		nS	VGS=0V
Qrr	Reverse Recovery Charge		5.7		μC	IS=25A,di/dt=100 A/µs

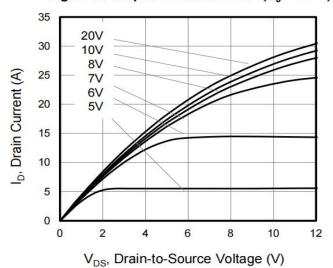
Notes:

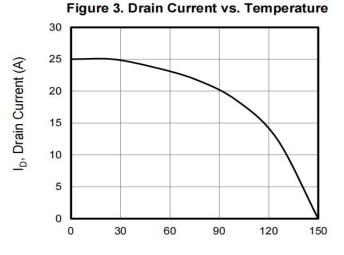
- * 1. Repetitive rating, pulse width limited by maximum junction temperature.
- * 2. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%



Typical Feature Curve

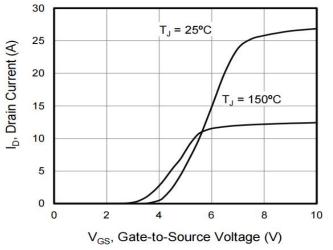
Figure 1. Output Characteristics (T_J = 25°C)





T_C, Case Temperature (A)

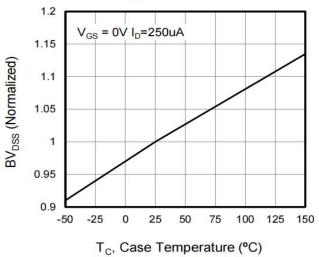




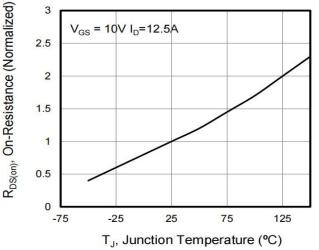
(V) $T_{J} = 150^{\circ}C$ $T_{J} = 25^{\circ}C$ 10^{0} 10^{-1} 0.2 0.4 0.6 0.8 1 1.2 1.4V_{SD}, Source-to-Drain Voltage (V)

Figure 2. Body Diode Forward Voltage

Figure 4. BV_{DSS} Variation vs. Temperature









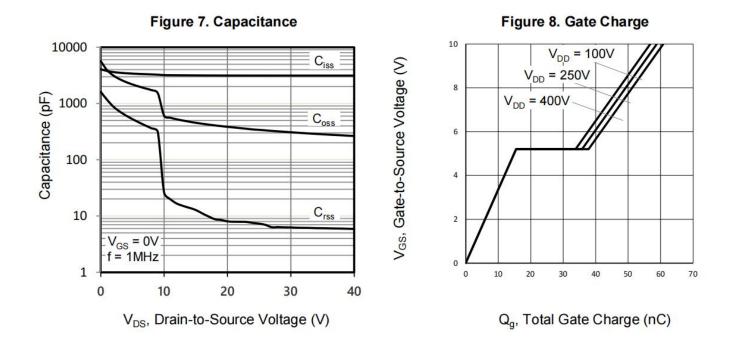
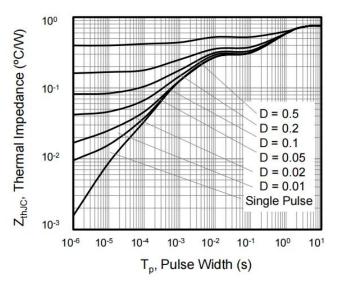


Figure 9. Transient Thermal Impedance





Test Circuits and Waveforms



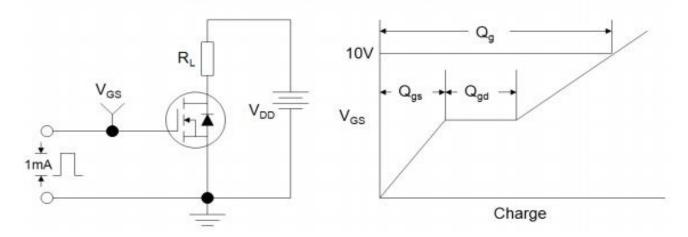


Figure B: Resistive Switching Test Circuit and Waveform

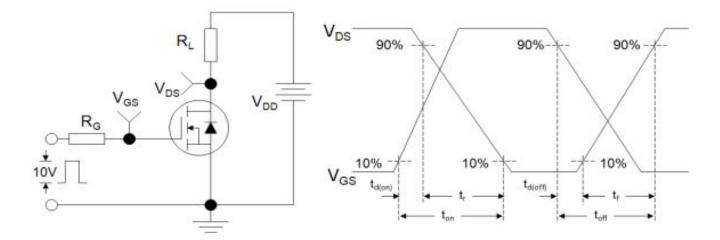
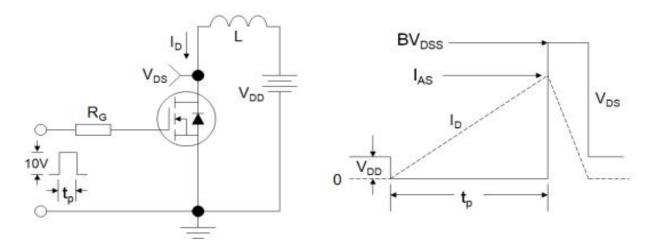
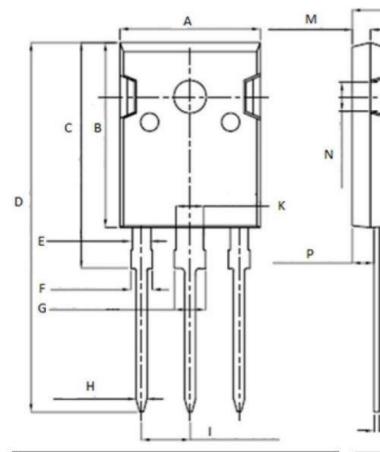


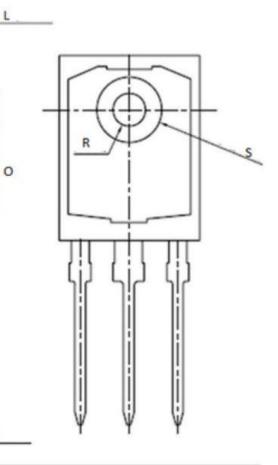
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





Package outline drawing(TO-247 Unit: mm)





	Unit: mm			Unit: mm	
Symbol	Min.	Max.	Symbol	Min.	Max.
Α	15.95	16.25	K	2.90	3.10
В	20.85	21.25	L	4.90	5.30
С	20.95	21.35	M	1.90	2.10
D	40.5	40.9	N	4.50	4.70
E	1.9	2.1	0	5.40	5.60
F	2.1	2.25	Р	2.29	2.49
G	3.1	3. 25	Q	0.51	0.71
Н	1.1	1.3	R	φ3.5	φ3.7
1	5.40	5.50	S	φ7.1	φ7.3

Q



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